



江苏朝图微电子有限公司

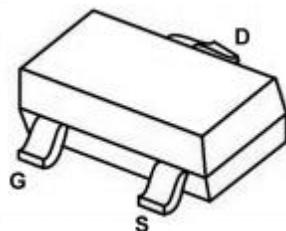
ZT2002KT

20V N-Channel MOSFET

## FEATURE

- $R_{DS(ON)} \leq 0.38\Omega$  ( 0.25 $\Omega$  Typ.)  
@ $V_{GS}=4.5V$
- $R_{DS(ON)} \leq 0.45\Omega$  ( 0.35 $\Omega$  Typ.)  
@ $V_{GS}=2.5V$
- $R_{DS(ON)} \leq 0.8\Omega$  ( 0.4 $\Omega$  Typ.)  
@ $V_{GS}=1.8V$

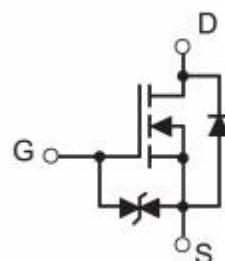
## SOT-523



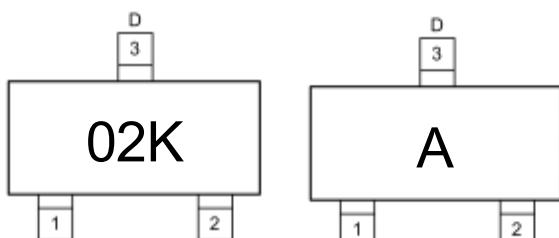
## APPLICATION

- Load/Power Switching
- Interfacing Switching

## CIRCUIT DIAGRAM



## MARKING



02K =Device Code

A =Device Code

**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

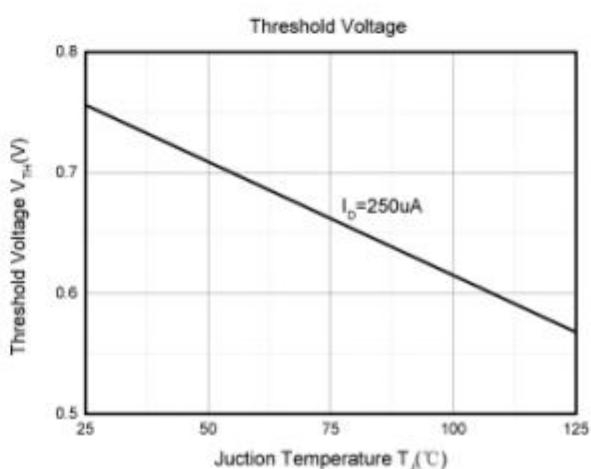
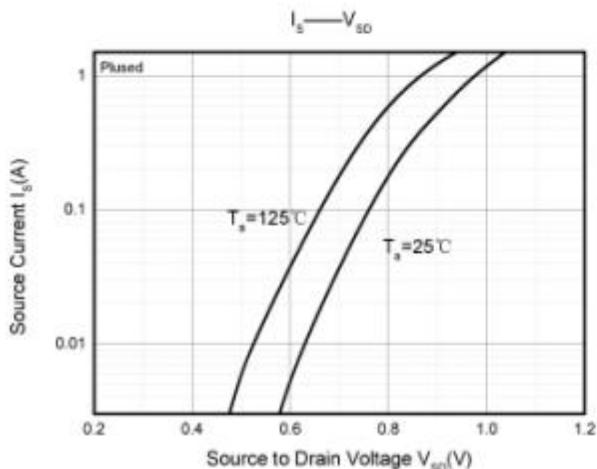
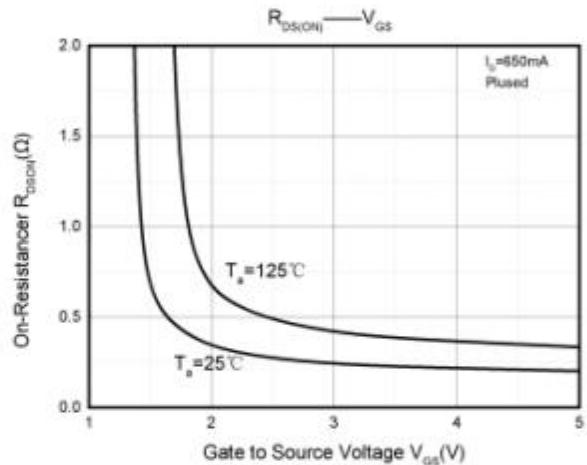
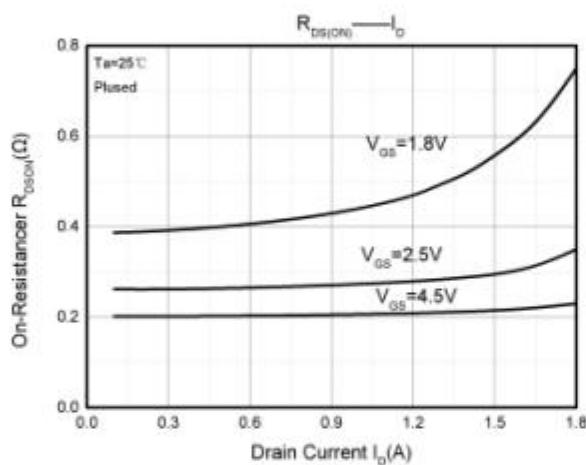
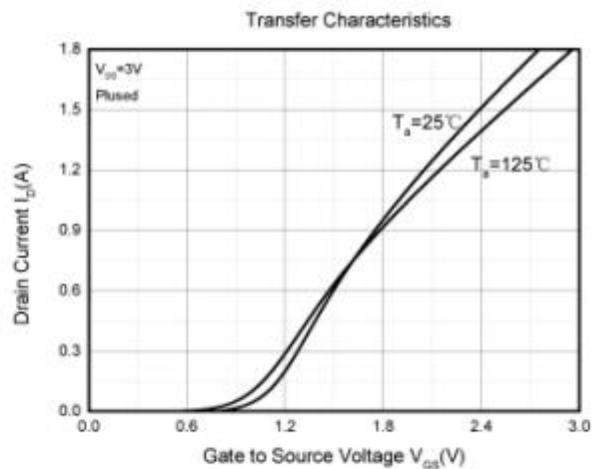
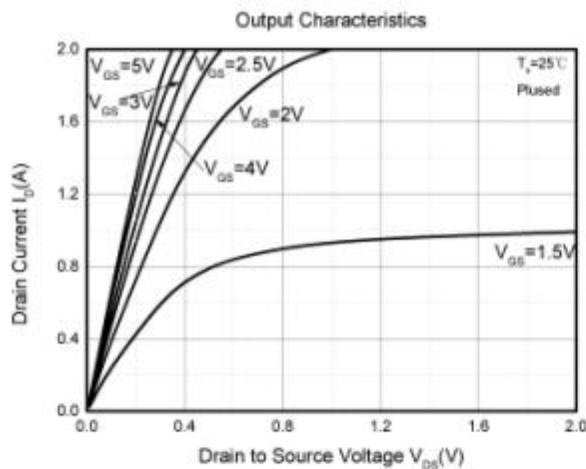
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±10	V
Continuous Drain Current	I <sub>D</sub>	0.75	A
Pulsed Drain Current	I <sub>DM</sub>	1.8	A
Power Dissipation	P <sub>D</sub>	0.15	W
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	833	C/W
Junction Temperature	T <sub>J</sub>	150	C
Storage Temperature	T <sub>STG</sub>	-55~+150	C

**Electrical characteristics (Ta=25 °C, unless otherwise noted)**

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	20			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V			1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V			±10	uA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.3	0.65	1	V
Drain-source on-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.5A		0.25	0.38	Ω
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 0.4A		0.35	0.45	
		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 0.1A		0.4	0.8	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.4A	0.8	-	-	S
<b>Dynamic characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, f = 1MHz		79	120	pF
Output Capacitance	C <sub>oss</sub>			13	20	
Reverse Transfer Capacitance	C <sub>rss</sub>			9	15	
<b>Switching Characteristics</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 500mA, R <sub>GEN</sub> = 10Ω		6.7		ns
Turn-on rise time	t <sub>r</sub>			4.8		
Turn-off delay time	t <sub>d(off)</sub>			17.3		
Turn-off fall time	t <sub>f</sub>			7.4		
<b>Source-Drain Diode characteristics</b>						
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 0.5A, V <sub>GS</sub> = 0V		0.7	1.3	V

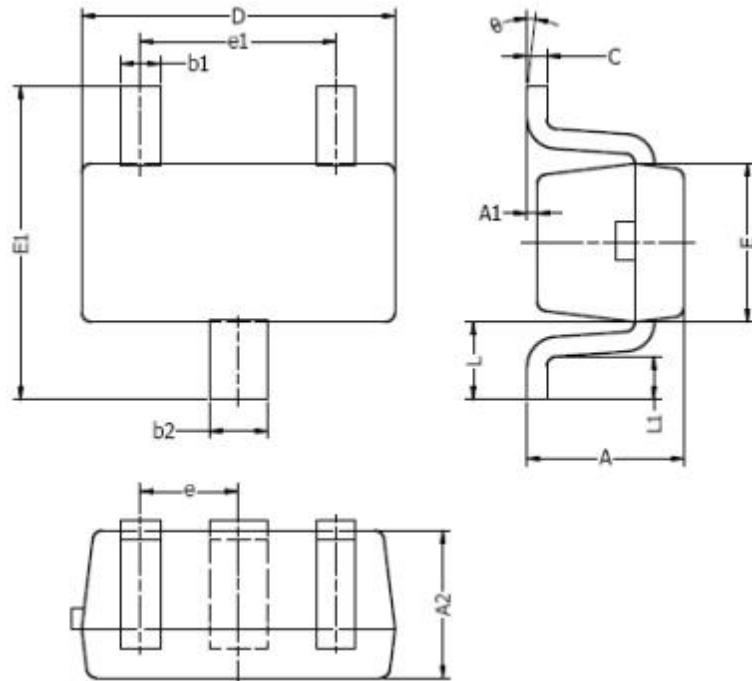


## Typical Characteristics





## SOT-523 Package Information



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
e	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
θ	0 °	8 °	0 °	8 °